

Claims

[c1] What is claimed is:

1.A method for fabricating a trench capacitor, comprising:

providing a substrate having thereon a pad layer;

etching in order of said pad layer and said substrate to form a deep trench;

doping said deep trench to form a buried diffusion plate in said substrate at a lower portion of said deep trench;

lining said deep trench with a node dielectric layer;

performing a first polysilicon deposition and recess etching to embed a first polysilicon (Poly1) layer on said node dielectric layer at said lower portion of said deep trench, and said first polysilicon (Poly1) layer having a top surface, wherein said top surface of said first polysilicon layer and sidewall of said deep trench define a first recess;

forming a collar oxide layer on sidewall of said first recess;

performing a second polysilicon deposition and recess etching to embed a second polysilicon (Poly2) layer on said first polysilicon (Poly1) layer;

forming a mask layer partially masking said collar oxide

layer;

removing said collar oxide layer not masked by said mask layer and said second polysilicon (Poly2) layer;

removing said mask layer; and

performing a third polysilicon deposition and recess etching to embed a third polysilicon (Poly3) layer on said second polysilicon (Poly2) layer.

[c2] 2.The method of claim 1 wherein said substrate is a silicon substrate.

[c3] 3.The method of claim 1 wherein said deep trench has a depth that is larger than 6 microns below a surface of said substrate.

[c4] 4.The method of claim 1 wherein doping said deep trench to form a buried diffusion plate in said substrate involves the use of an arsenic silicate glass (ASG) film.

[c5] 5.The method of claim 1 wherein said node dielectric is an oxide–nitride–oxide (ONO) dielectric layer.

[c6] 6.The method of claim 1 wherein said mask layer comprises a photoresist layer.

[c7] 7.The method of claim 6 wherein said mask layer further comprises a sacrificial layer underlying said photoresist layer.

[c8] 8.The method of claim 7 wherein said sacrificial layer is made of anti-reflection coating materials.